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	Applicant(s): Hiroji EBE, et al.	
	Filing Date: September 16, 2003	Group Art Unit: Not Yet Assigned


U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)	
<u>DF</u>	AE	9-326506	12/16/97	Japan	Yes-Abstract/Discussed in the specification
_____	AF				

OTHER DOCUMENTS

<u>DF</u>	AG	D. Leonard et al.; "Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces"; <i>Applied Physics Letters</i> ; Vol. 63; No. 23; December 6 1993; pp. 3203-3205./Discussed in the specification.
<u>DF</u>	AH	K. Mukai et al.; "Self-Formed In _{0.5} Ga _{0.5} As Quantum Dots on GaAs Substrates Emitting at 1.3μm"; <i>Japanese Journal of Applied Physics</i> Vol. 33; Part 2, No. 12A; December 1 1994; pp. L1710-1712./Discussed in the specification.
<u>DF</u>	AI	J. Oshinowo et al.; "Highly uniform InGaAs/GaAs quantum dots (~15 nm) by metalorganic chemical vapor deposition"; <i>Applied Physics Letters</i> ; Vol. 65; No. 11; September 12 1994; pp. 1421-1423./Discussed in the specification.
Examiner		
Date Considered	11 / 30 / 05	